



HY100N03

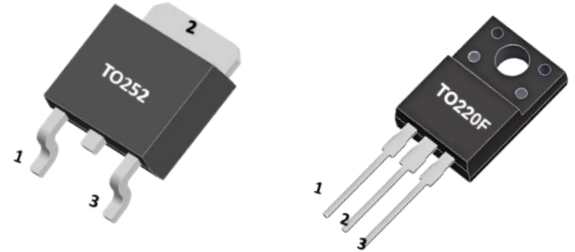
N-CHANNEL POWER MOSFET

100A, 30V N-CHANNEL ENHANCEMENT MODE POWER MOSFET

DESCRIPTION

The XD100N03Y uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with low gate voltages. This device is suitable for use as a load switch or in PWM applications.

The XD100N03Y meet the ROHS and Green Product requirement with full function reliability approved.



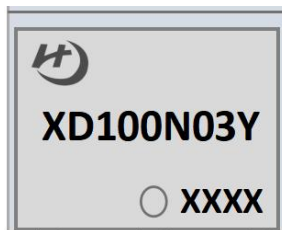
FEATURE

- * Excellent package for good heat dissipation
- * Ultra low gate charge
- * Low reverse transfer capacitance
- * Fast switching capability
- * Avalanche energy specified

APPLICATIONS

- * Power switching application

MARKING



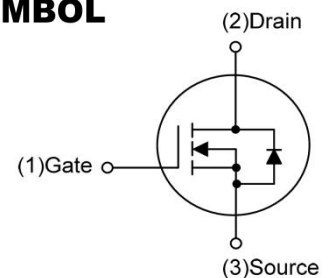
: HY LOGO

XD100N03Y=Device Code

XXXX=Date Code

Solid Dot=Green molding compound

SYMBOL



ABSOLUTE MAXIMUM RATINGS($T_A=25^\circ\text{C}$, unless otherwise specified.)

SYMBOL	PARAMETER		VALUE	UNIT
VDSS	Drain-Source Voltage		30	V
VGSS	Gate Source Voltage		± 20	V
ID	Continuous Drain Current		100	A
IDM	Pulsed Drain Current (Note 2)		400	A
IAS	Single Pulsed Avalanche Current (Note 3)		35	A
EAS	Single Pulsed Avalanche Energy(Note 3)		875	mJ
PD	Power Dissipation	TO-220F	36	W
		TO-252	50	
TJ	Storage Temperature		150	$^\circ\text{C}$
TSTG	Thermal Resistance Fr .00m Junction To Ambient		-55~150	$^\circ\text{C}$

Notes: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.



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■ THERMAL DATA

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient	TO-220F	θ_{JA}	62.5	°C/W
	TO-252		110	
Junction to Case	TO-220F	θ_{JC}	3.47	°C/W
	TO-252		2.5	

■ ELECTRICAL CHARACTERISTICS ($T_A=25^{\circ}\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250μA	30			V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =30V, V _{GS} =0V			1	μA
Gate-Source Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±20V			±100	nA
ON CHARACTERISTICS(Note2)						
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} =V _{GS} , I _D =250μA	1.0		3.0	V
Static Drain-Source On-Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =50A		3.05	5.3	mΩ
		V _{GS} =4.5V, I _D =40A		4.2	8.0	mΩ
		V _{GS} =4.5V, I _D =40A		4.2	5.8	mΩ
DYNAMIC PARAMETERS(Note3)						
Input Capacitance	C _{ISS}	V _{DS} =15V, V _{GS} =0V f=1.0MHz		5200		pF
Output Capacitance	C _{OSS}			1040		
Reverse Transfer Capacitance	C _{RSS}			900		
SWITCHING PARAMETERS(Note3)						
Total Gate Charge	Q _G	V _{DS} =15V, V _{GS} =5V I _D =16A (Note 1, 2)		81		nC
Gate Source Charge	Q _{GS}			20		
Gate Drain Charge	Q _{GD}			37		
Turn-ON Delay Time	t _{D(ON)}	V _{DD} =15V, I _D =16A R _G =6Ω V _{GS} =10V (Note 1, 2)		22		ns
Turn-ON Rise Time	t _R			25		
Turn-OFF Delay Time	t _{D(OFF)}			128		
Turn-OFF Fall-Time	t _F			73		
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Drain-Source Diode Forward Current	I _S				90	A
Maximum Body-Diode Pulsed Current	I _{SM}				180	A
Drain-Source Diode Forward Voltage	V _{SD}	I _S =20A, V _{GS} =0V			1.5	V

Notes: 1.Pulse Test : Pulse Width < 300 μ s, Duty Cycle < 2%.

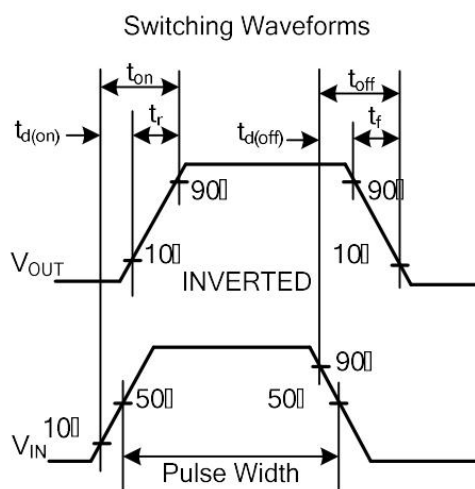
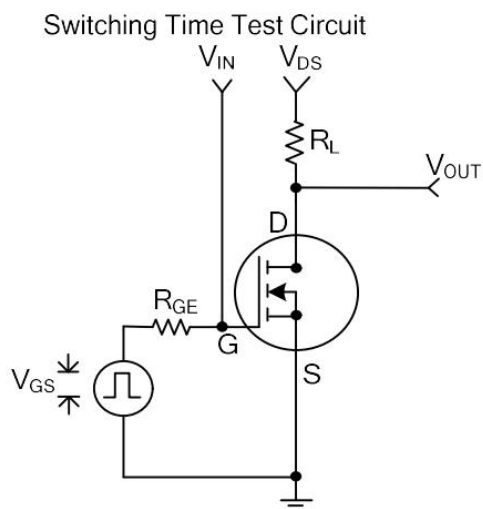
2.Guaranteed by design, not subject to production testing.



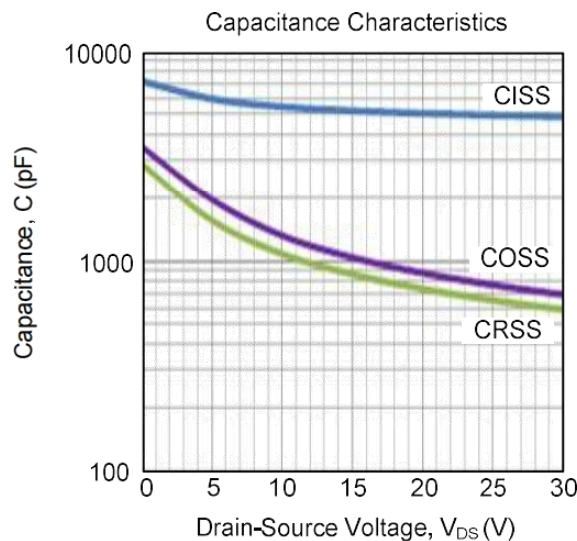
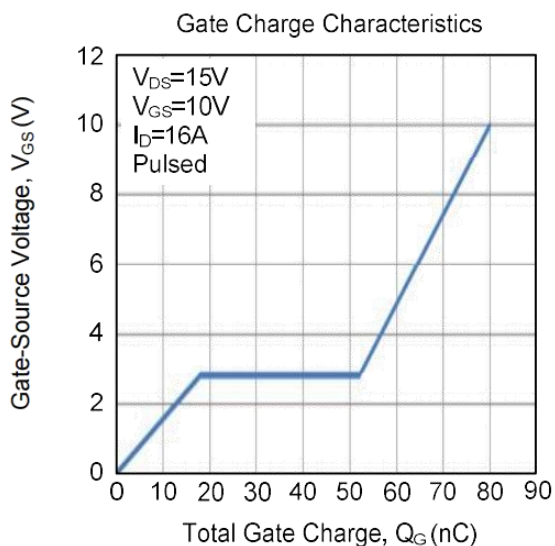
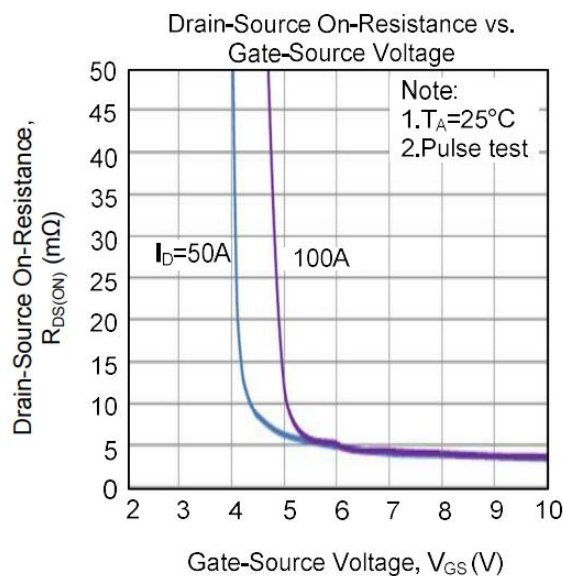
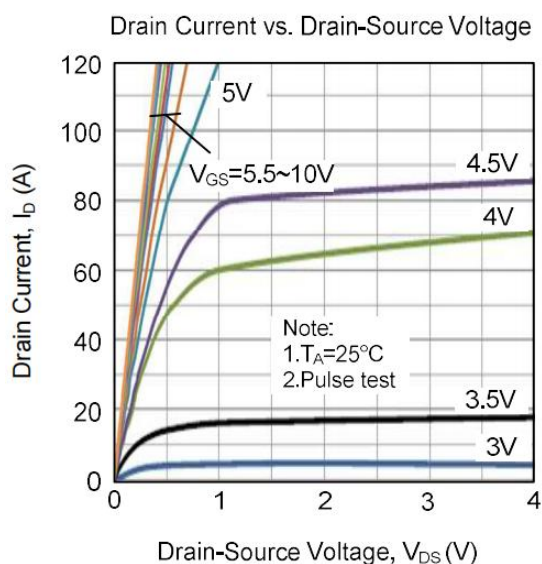
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■ TEST CIRCUITS AND WAVEFORMS



■ TYPICAL CHARACTERISTICS

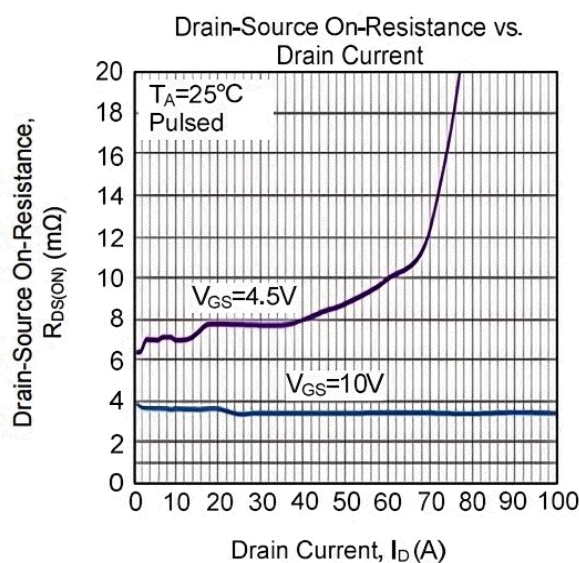
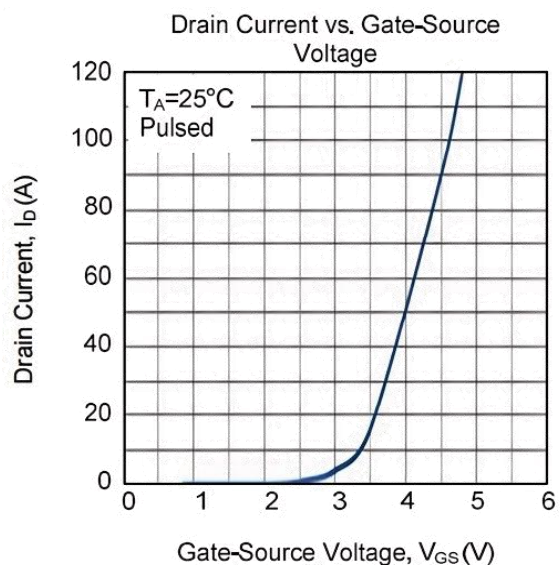
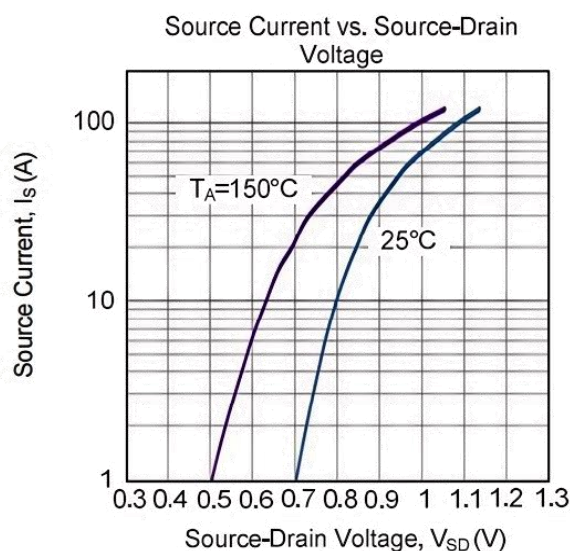
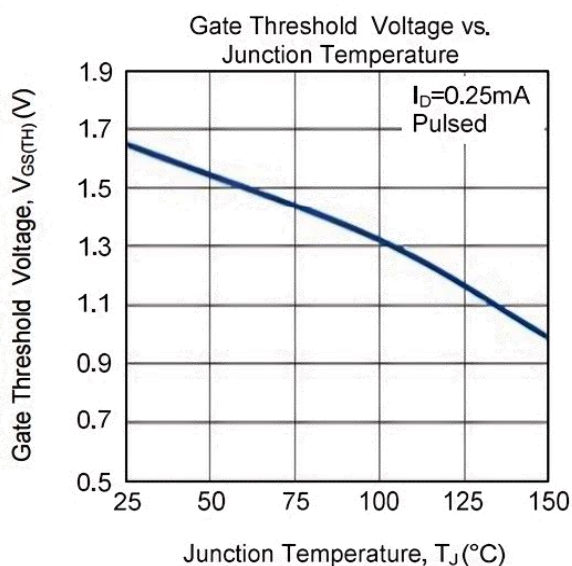
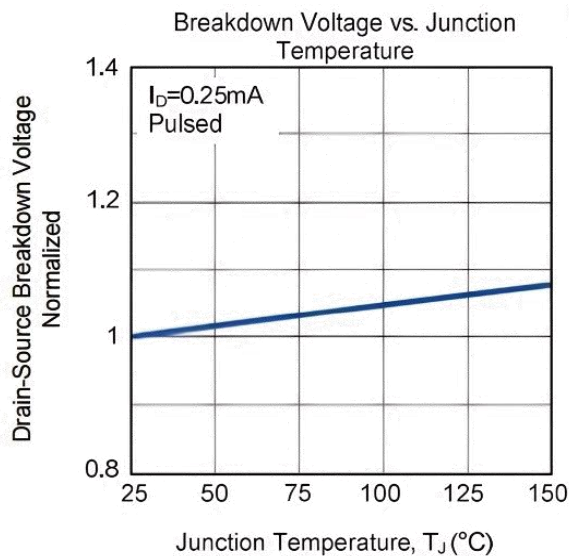
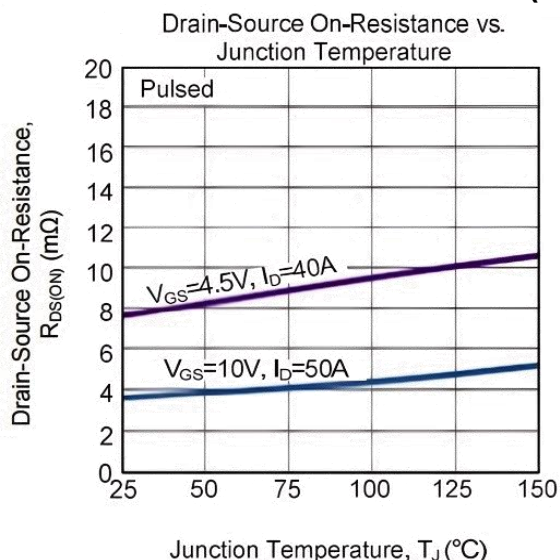




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■ TYPICAL CHARACTERISTICS(Con.t)

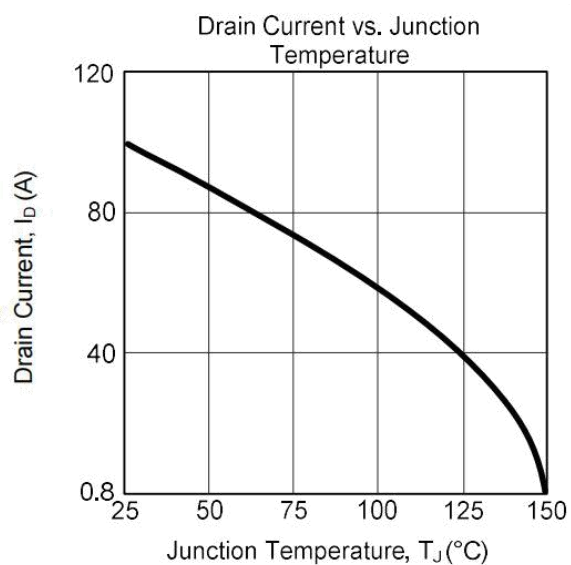




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■ **TYPICAL CHARACTERISTICS(Con.t)**

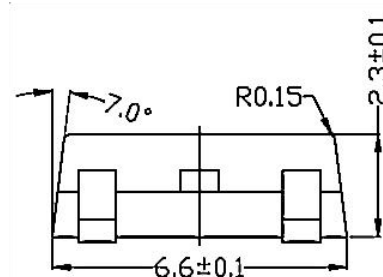
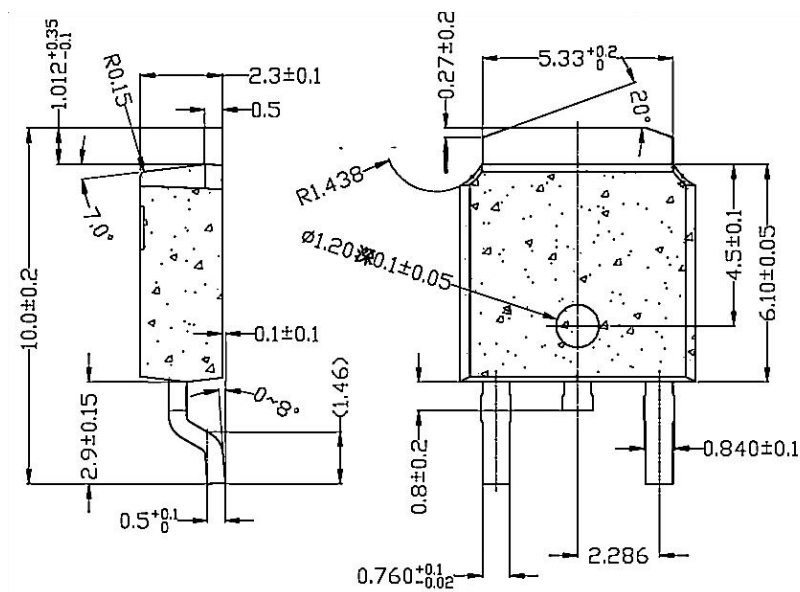




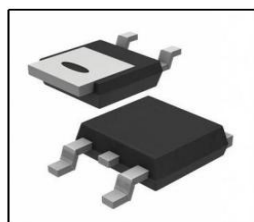
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N-CHANNEL POWER MOSFET

TO - 252 PACKAGE OUTLINE DIMENSIONS



TO - 252 PACKING INFORMATION



2500PC
S/reel



2 Reel/BOX



Outer box

5 Inner
Box



Inner box

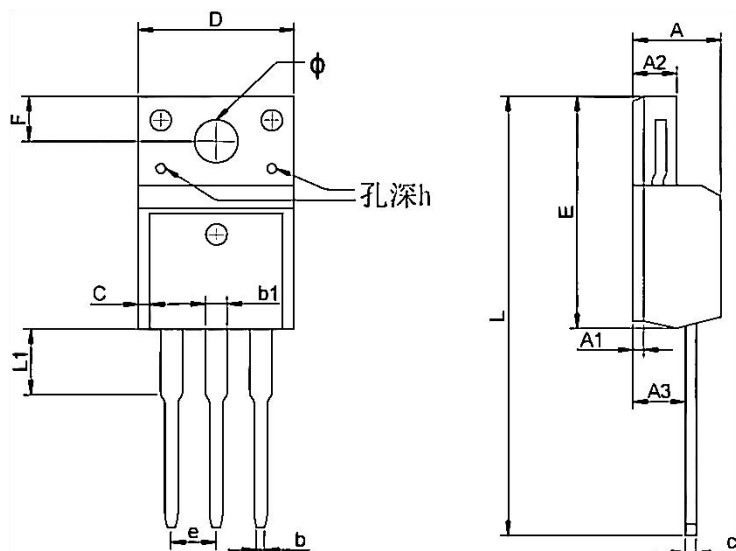
Package version	Reel dimensions $\Phi \times H$ (mm)	Per Reel (pcs)	Reels per box	Inner box dimensions $L \times W \times H$ (mm)	Outer box (pcs)	Outer box dimensions $L \times W \times H$ (mm)
TO-252	$\Phi 330 \times 20$	2500	2	360*340*50	25000	375*375*280



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TO-220F PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.300	4.750	0.169	0.185
A1	1.830 REF		0.072 REF	
A2	2.300	2.850	0.090	0.112
A3	2.500	2.900	0.098	0.114
b	0.400	0.420	0.016	0.016
b1	1.220	1.280	0.048	0.050
C	0.690	0.720	0.027	0.028
c	0.490	0.510	0.019	0.020
D	9.960	10.200	0.392	0.400
E	15.000	15.950	0.588	0.625
e	2.574 TYP		0.101TYP	
F	3.470 REF		0.136 REF	
y	3.200 REF		0.125 REF	
h	0.000	0.300	0.000	0.012
L	28.780	28.900	1.128	1.133
L1	2.990	3.100	0.117	0.122

TO - 220F PACKING INFORMATION



50PCS

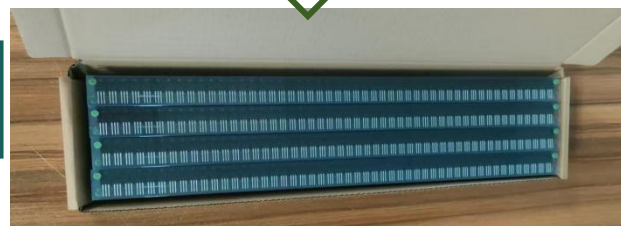


20 Tube



Outer Box

5 Inner
Box



Inner Box

Package version	Tube dimensions LxW×H (mm)	Per Tube (pcs)	Tube per box	Inner box dimensions LxW×H (mm)	PCS/ Inner box	Outer box dimensions L×W×H(mm)	PCS/ Outer box
TO-220F	530*32*7	50	20	580*155*50	1000	602*277*188	5000